BTA204-800B



3Q Hi-Com Triac Rev. 03 — 9 May 2011

Product data sheet

1. **Product profile**

1.1 General description

Planar passivated high commutation three quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. This "series B" triac will commutate the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

1.2 Features and benefits

- 3Q technology for improved noise immunity
- High blocking voltage capability
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- Less sensitive gate for very high noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

1.3 Applications

- General purpose motor control circuits
- Home appliances

Rectifier-fed DC inductive loads e.g. DC motors and solenoids

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	-	25	Α
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 107 °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	-	4	Α



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	-	-	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	-	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{\text{Im}}$	-	-	50	mA

2. Pinning information

Table 2. Pinning information

	9			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		N.1
2	T2	main terminal 2	mb	T2—T1
3	G	gate		sym051
mb	T2	mounting base; main terminal 2		
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	number Package			
	Name	Description	Version	
BTA204-800B	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

SymbolParameterConditionsMinMax V_{DRM} repetitive peak off-state voltage-800 $I_{T(RMS)}$ RMS on-state currentfull sine wave; $T_{mb} \le 107$ °C; see Figure 1;-4	Unit V A
$I_{T(RMS)}$ RMS on-state current full sine wave; $T_{mb} \le 107$ °C; see Figure 1; - 4	Α
see Figure 2; see Figure 3	
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	Α
full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 16.7 \text{ms}$ - 27	Α
I^2t I^2t for fusing $t_p = 10$ ms; sine-wave pulse - 3.1	A ² s
dI_T/dt rate of rise of on-state current $I_T = 6$ A; $I_G = 0.2$ A; $dI_G/dt = 0.2$ A/ μ s - 100	A/µs
I _{GM} peak gate current - 2	Α
P _{GM} peak gate power - 5	W
P _{G(AV)} average gate power over any 20 ms period - 0.5	W
T _{stg} storage temperature -40 150	°C
T _j junction temperature - 125	°C

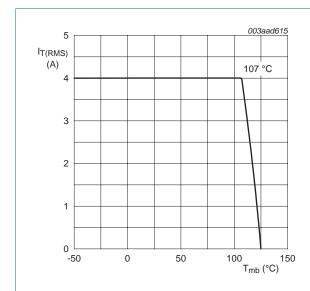
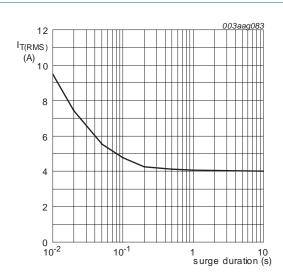


Fig 1. RMS on-state current as a function of mounting base temperature; maximum values



f = 50 Hz; T_{mb} = 107 °C

Fig 2. RMS on-state current as a function of surge duration; maximum values

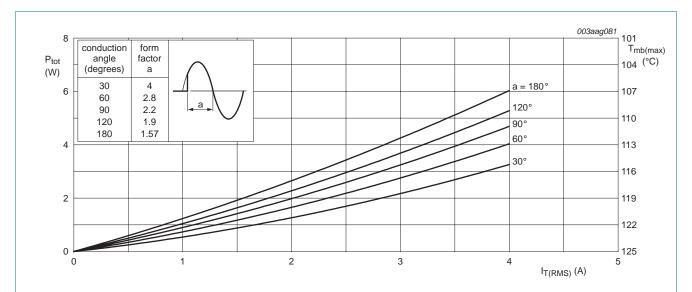


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

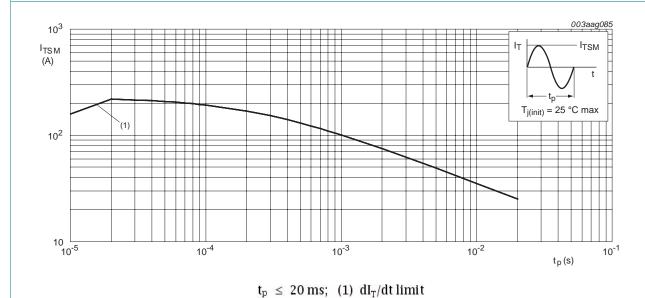


Fig 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

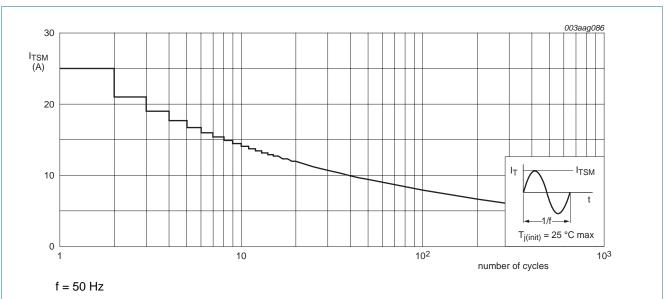
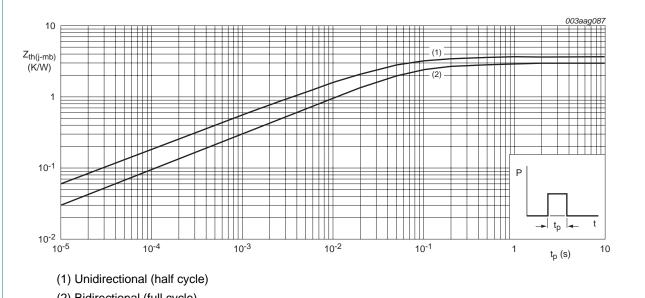


Fig 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

Thermal characteristics

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to	full cycle; see Figure 6	-	-	3	K/W
	mounting base	half cycle; see Figure 6	-	-	3.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W



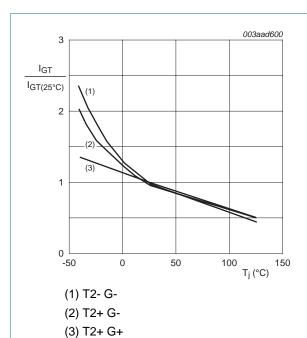
(2) Bidirectional (full cycle)

Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse width

6. Characteristics

Table 6. Characteristics

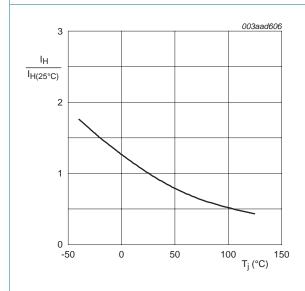
Table 0.	Onaracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT} gate trigger current	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+G+; T_j = 25 \text{ °C;}$ see Figure 7	-	-	50	mA
	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+\text{ G-; } T_j = 25 \text{ °C;}$ see Figure 7	-	-	50	mA	
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-; } T_j = 25 \text{ °C;}$ see Figure 7	-	-	50	mA
I _L latching current	$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 8}}{}$	-	-	30	mA	
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2 + G-; T_j = 25 \text{ °C;}$ see Figure 8	-	-	45	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-}; T_j = 25 \text{ °C};$ see Figure 8	-	-	30	mA
I _H	holding current	$V_D = 12 \text{ V; } T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{}$	-	-	30	mΑ
V_{T}	on-state voltage	$I_T = 5 \text{ A}$; $T_j = 25 \text{ °C}$; see <u>Figure 10</u>	-	1.4	1.7	V
V _{GT} gat	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T_j = 25 \text{ °C;}$ see Figure 11	-	0.7	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ see Figure 11	0.25	0.4	-	V
I _D	off-state current	$V_D = 800 \text{ V}; T_j = 125 ^{\circ}\text{C}$	-	0.1	0.5	mΑ
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; exponential waveform; gate open circuit	1000	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V; } T_j = 125 \text{ °C; } I_{T(RMS)} = 4 \text{ A;}$ $dV_{com}/dt = 20 \text{ V/}\mu\text{s; snubberless}$ condition; gate open circuit	6	-	-	A/ms
t _{gt}	gate-controlled turn-on time	$I_{TM} = 12 \text{ A}; V_D = 800 \text{ V}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs



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Fig 7. Normalized gate trigger current as a function of junction temperature

Fig 8. Normalized latching current as a function of junction temperature



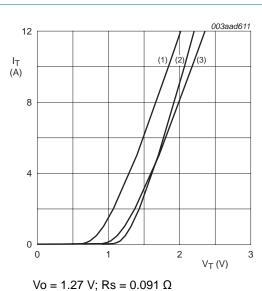
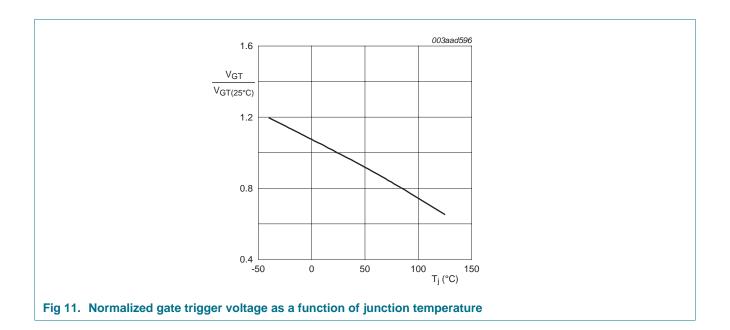


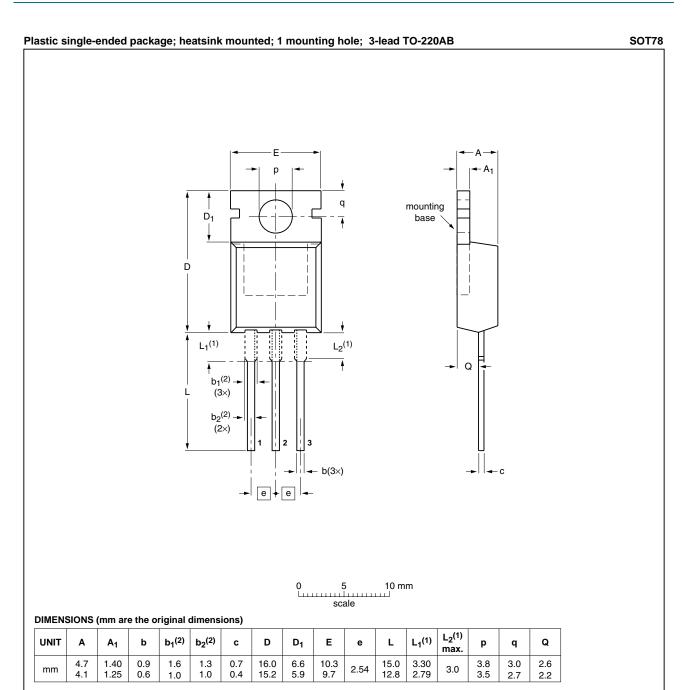
Fig 9. Normalized holding current as a function of junction temperature

(1) Tj = 125 °C; typical values (2) Tj = 125 °C; maximum values (3) Tj = 25 °C; maximum values

Fig 10. On-state current as a function of on-state voltage



7. Package outline



Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig 12. Package outline SOT78 (TO-220AB)

BTA204-800B

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA204-800B v.3	20110509	Product data sheet	-	BTA204_SERIES_B_C v.2
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 			
	 Legal texts have 	ave been adapted to the r	new company name	where appropriate.
	 Type number 	BTA204-800B separated	from data sheet BT	A204_SERIES_B_C v.2.
BTA204_SERIES_B_C v.2	19981201	Product specification	-	BTA204_SERIES_B_C v.1

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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